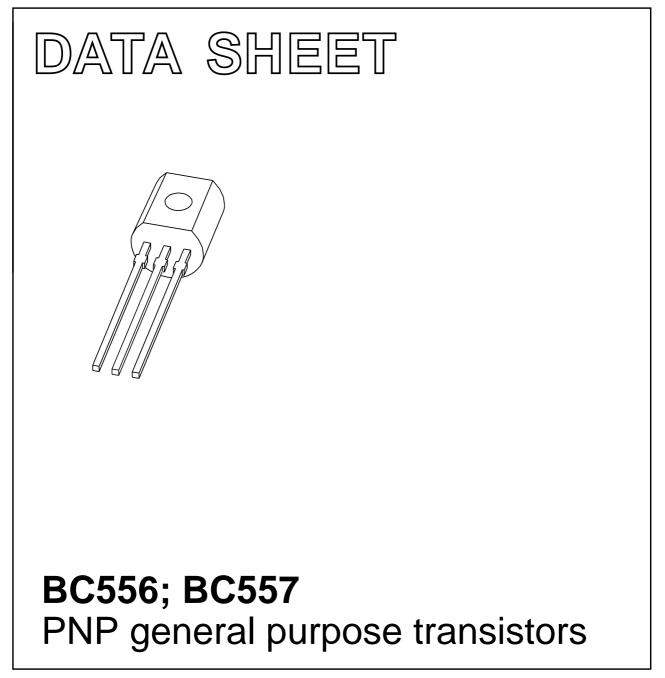
# DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1999 Apr 15

2004 Oct 11



### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

### APPLICATIONS

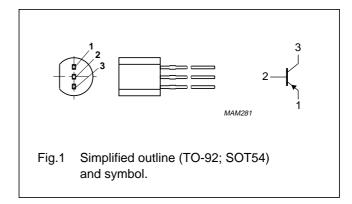
• General purpose switching and amplification.

### DESCRIPTION

PNP transistor in a TO-92; SOT54 plastic package. NPN complements: BC546 and BC547.

### PINNING

PIN	DESCRIPTION	
1	emitter	
2	base	
3	collector	



### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE			
ITFE NUMBER	NAME	DESCRIPTION	VERSION		
BC556	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54		
BC557					

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC556		_	-80	V
	BC557		_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC556		_	-65	V
	BC557		-	-45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
I <sub>C</sub>	collector current (DC)		-	-100	mA
I <sub>CM</sub>	peak collector current		_	-200	mA
I <sub>BM</sub>	peak base current		-	-200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

### BC556; BC557

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	250	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

### CHARACTERISTICS

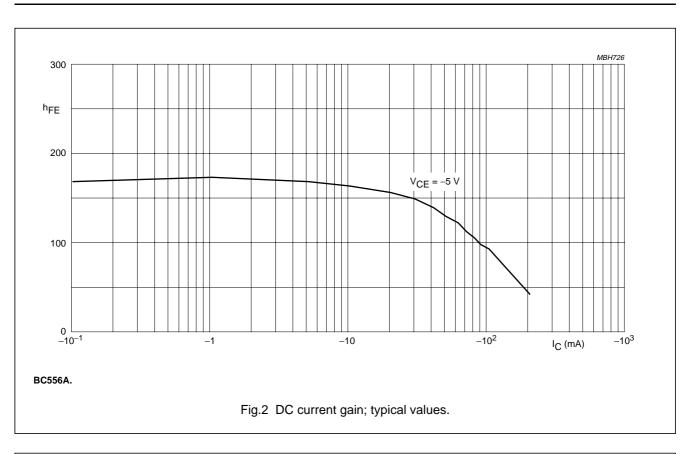
 $T_{amb}$  = 25 °C unless otherwise specified.

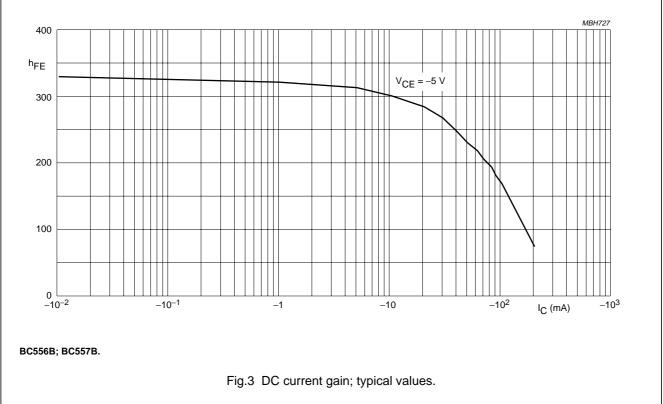
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V}; \text{ I}_{\text{E}} = 0 \text{ A}$	-	-1	-15	nA
		$V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	-4	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ V}$	_	-	-100	nA
h <sub>FE</sub>	DC current gain	$I_{C} = -2 \text{ mA}; V_{CE} = -5 \text{ V};$				
	BC556	see Figs 2, 3 and 4	125	-	475	
	BC557		125	-	800	
	BC556A		125	-	250	
	BC556B; BC557B		220	-	475	
	BC557C		420	-	800	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{\rm C} = -10 \text{ mA}; I_{\rm B} = -0.5 \text{ mA}$	_	-60	-300	mV
		$I_{\rm C} = -100 \text{ mA}; I_{\rm B} = -5 \text{ mA}$	_	-180	-650	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C} = -10 \text{ mA}; I_{B} = -0.5 \text{ mA}; \text{ note } 1$	-	-750	-	mV
		$I_{\rm C} = -100 \text{ mA}; I_{\rm B} = -5 \text{ mA}; \text{ note } 1$	-	-930	-	mV
V <sub>BE</sub>	base-emitter voltage	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}; \text{ note } 2$	-600	-650	-750	mV
		$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; \text{ note } 2$	-	-	-820	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	-	3	-	pF
Ce	emitter capacitance	$V_{EB} = -0.5 \text{ V}; I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$	_	10	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; I_C = -10 \text{ mA}; f = 100 \text{ MHz}$	100	_	_	MHz
F	noise figure	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -200 \mu\text{A}; \text{ R}_{S} = 2 k\Omega;$ f = 1 kHz; B = 200 Hz	-	2	10	dB

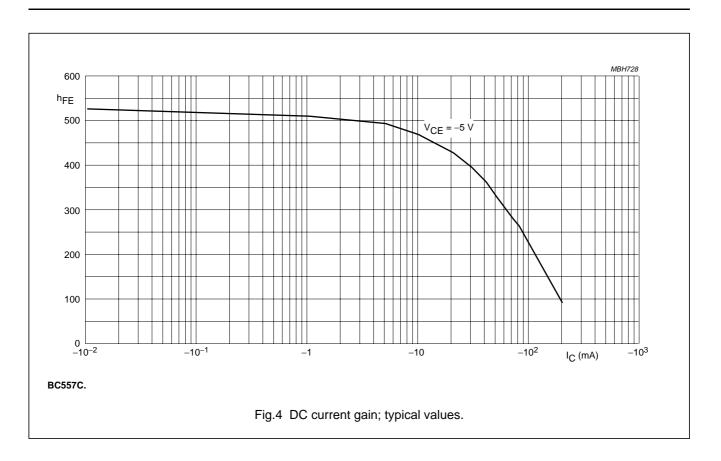
### Notes

1.  $V_{BEsat}$  decreases by about –1.7 mV/K with increasing temperature.

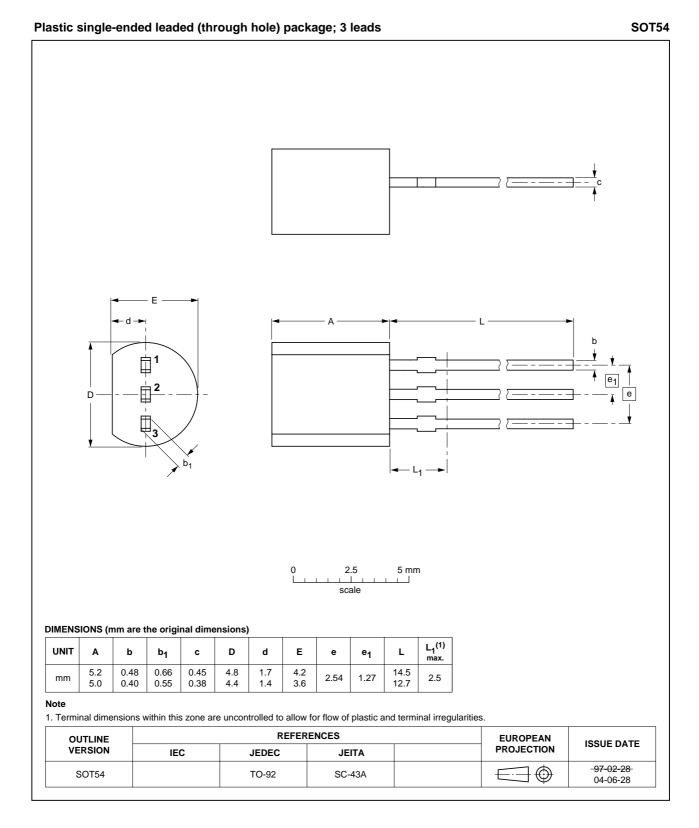
2.  $V_{BE}$  decreases by about –2 mV/K with increasing temperature.







### PACKAGE OUTLINE



BC556; BC557

### DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

#### DEFINITIONS

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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